

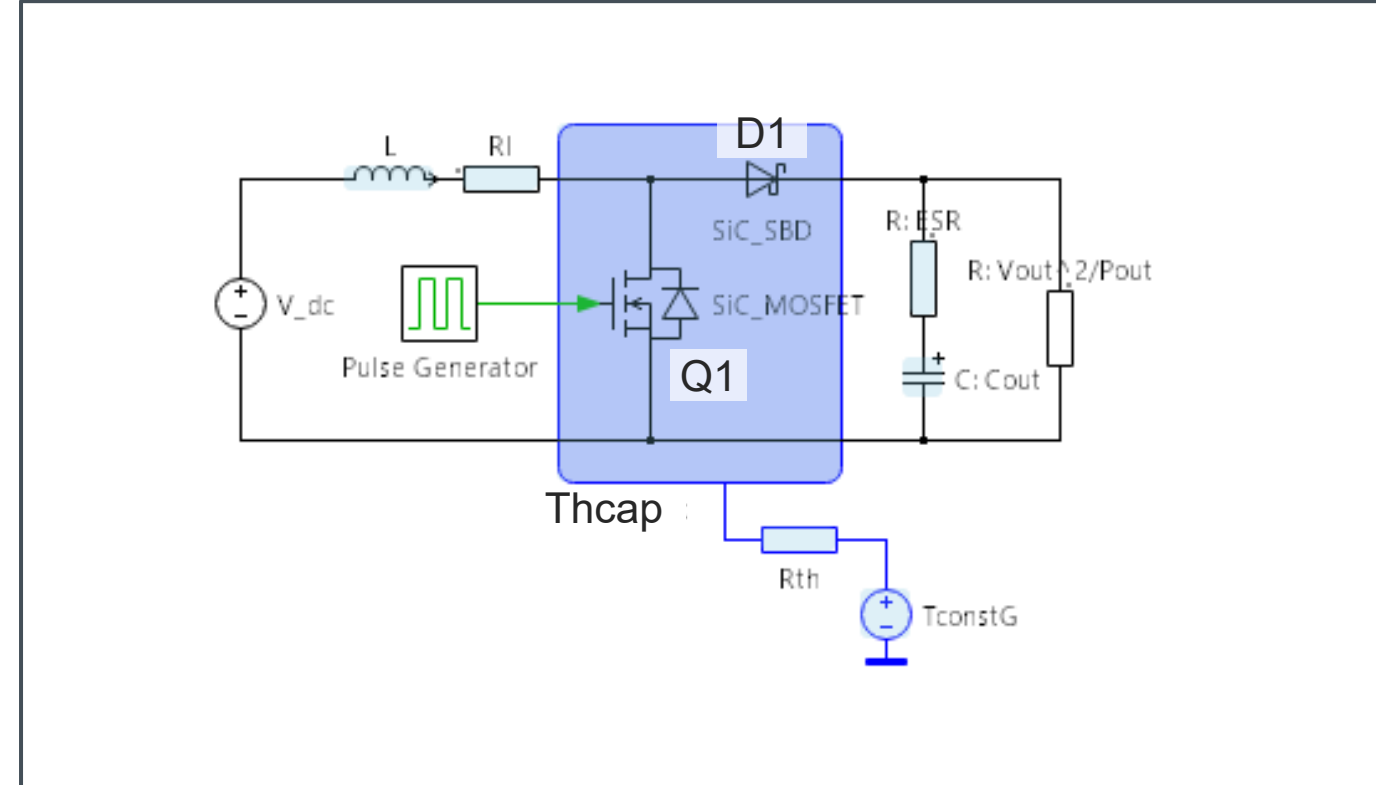
(C-002-D) DC-DC Boost Converter (Discrete)

Simulation Parameters

Name	Content	unit	Default Value	Variable Range
L	Inductive Load	H	1.2m	1n ~ 1
RI	Parasitic Resistance	Ω	100m	1u ~ 100m
Cout	Output Capacitor	F	100u	1n ~ 1
Vc_init	Initial Voltage of Cout	V	500	0 ~ 1200
ESR	Equivalent Series Resistance	Ω	10m	1u ~ 100m
Rth	Thermal Resistance	K/W	0.5	1m ~ 100
Thcap	Thermal Capacitance	J/K	10m	1m ~ 100
TGND	Thermal GND Temperature	$^{\circ}\text{C}$	25	-40 ~ 175

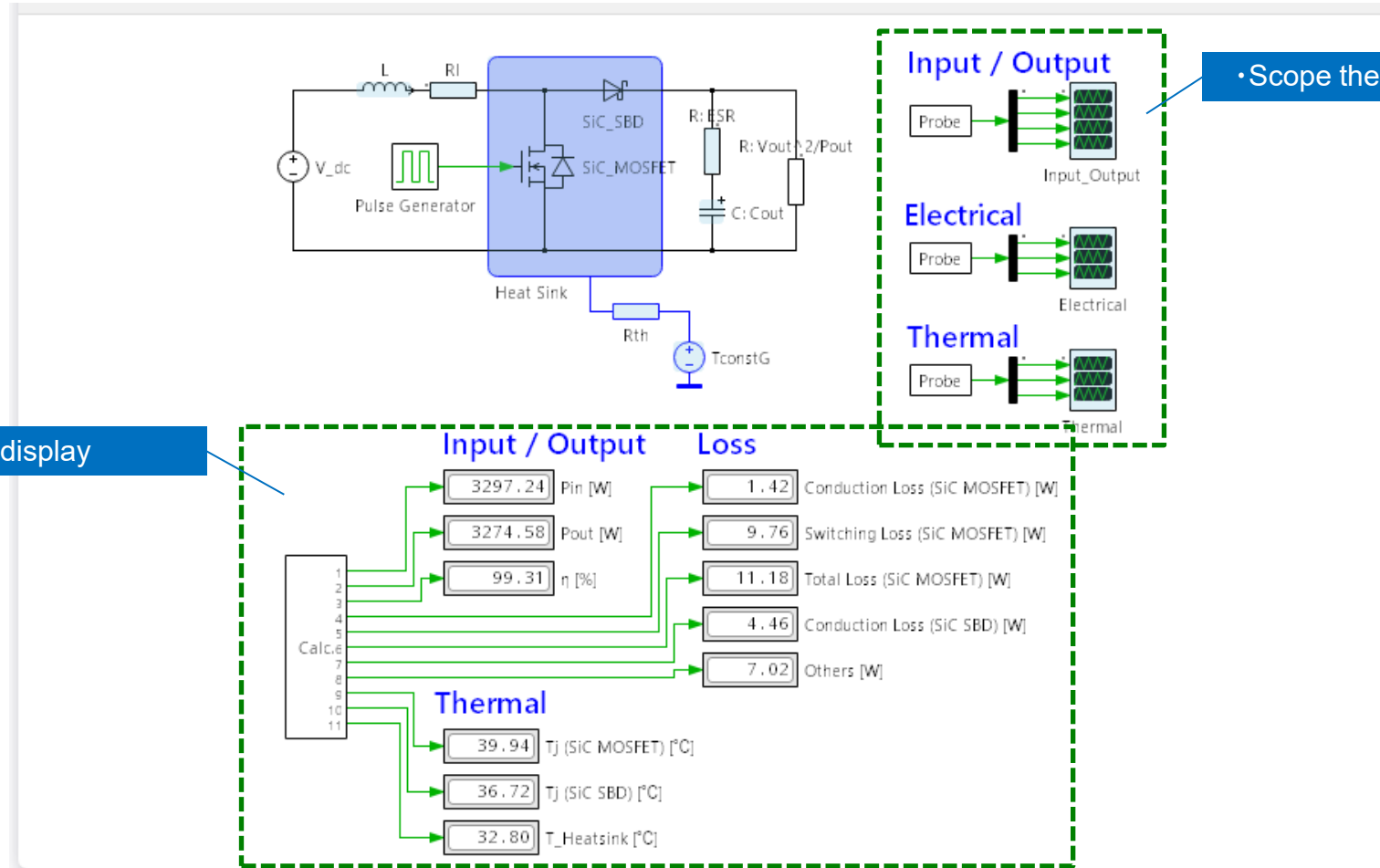
Name	Content	unit	Default Value	Variable Range
Test_time	Test time in simulation	s	0.3	100u ~ 0.5
fs	Switching Frequency	Hz	50k	10k ~ 100k
Vin	Input Voltage	V	400	1 ~ 1000
Vout	Output Voltage	V	800	10 ~ 1200
Pout	Output Power	W	3.3k	1 ~ 10k
Rg_on	Gate Resistance (Source)	Ω	10	0.1 ~ 100
Rg_off	Gate Resistance (Sink)	Ω	3.3	0.1 ~ 100
T_init	Initial Junction Temperature	$^{\circ}\text{C}$	25	-40 ~ 175

Simulation Circuit



Name	Device Type	Part No.	Specification
Q1	SiC MOSFET	SCT4036KR	1200V/ 43A/ 36m Ω / TO-247-4L
D1	SiC Schottky Barrier Diode	SCS320AG	650V/ 20A/ TO-220ACGE

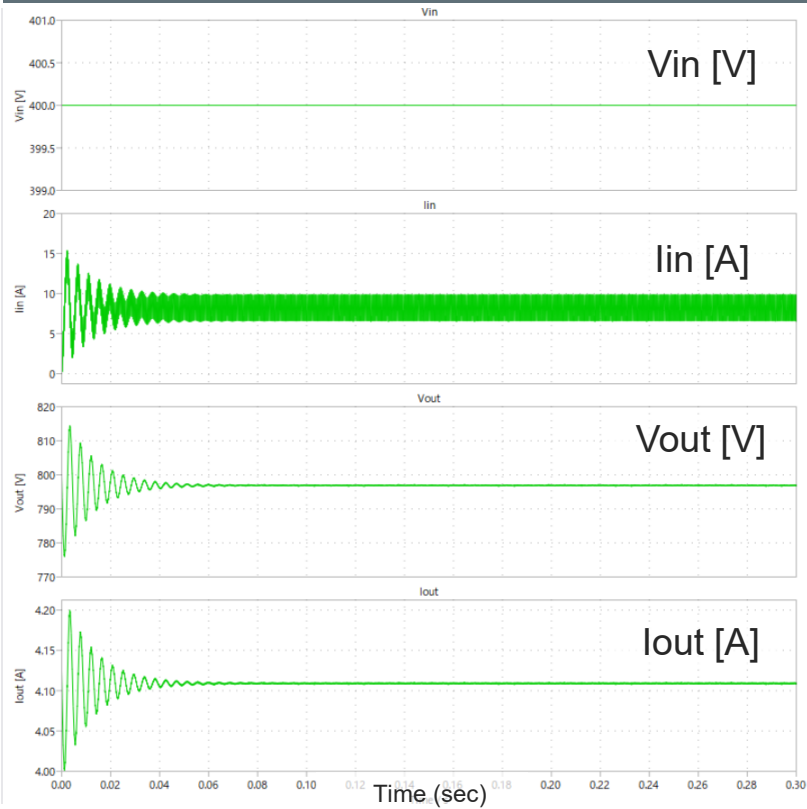
Schematic window



• Results display

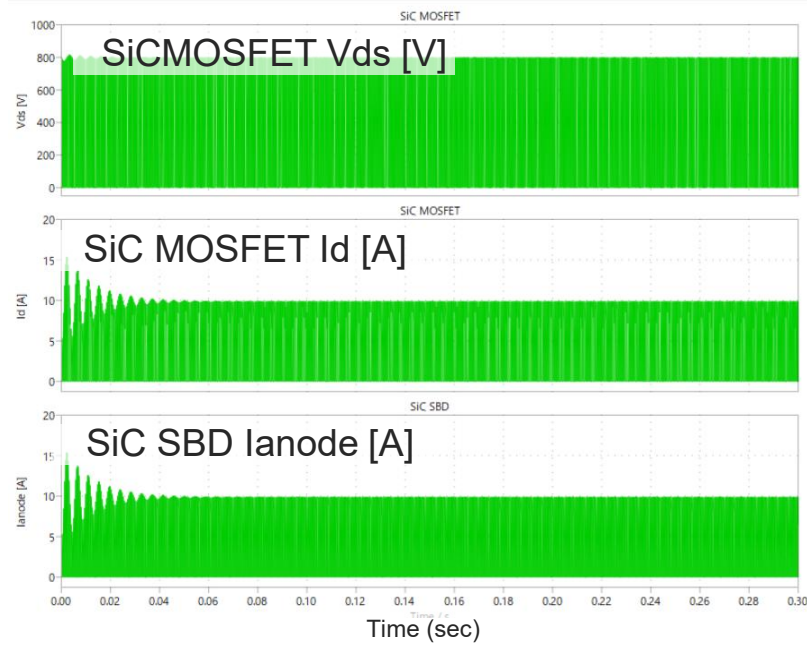
• Scope the waveform

Input and Output



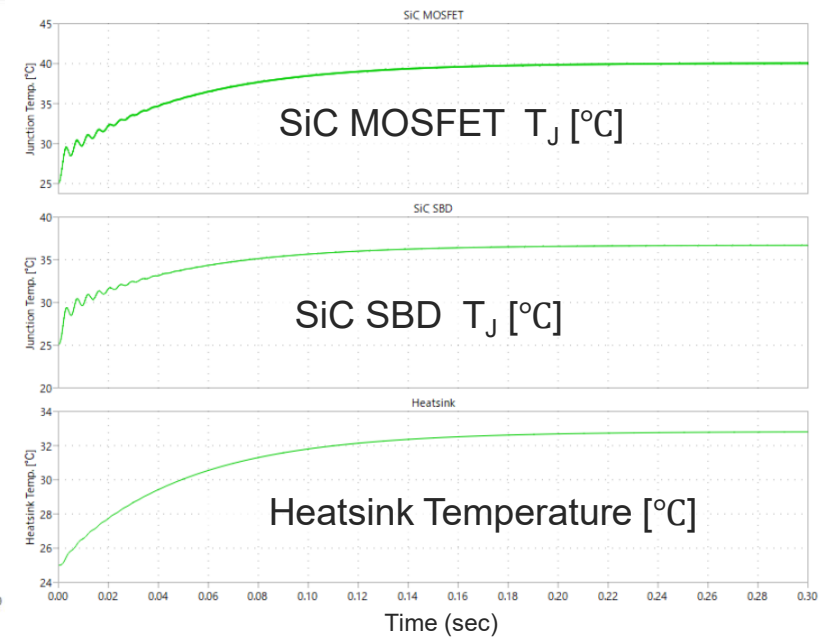
Contents	Results
Input Power : Pin	3.297 kW
Output Power: Pout	3.275 kW
Efficiency: η	99.31 %

Electrical



Contents	Results
Conduction Loss (SiC MOSFET)	1.42 W
Switching Loss (SiC MOSFET)	9.76 W
Total Loss (SiC MOSFET)	11.18 W
Conduction Loss (SiC SBD)	4.46 W
Loss (Others)	7.02 W

Thermal



Contents	Results
Tj (SiC MOSFET)	39.94 °C
Tj (SiC SBD)	36.72 °C
T_Heatsink	32.80 °C

To run this PLECS Reference Circuit, you must have the "PLECS" simulation software installed on your computer.

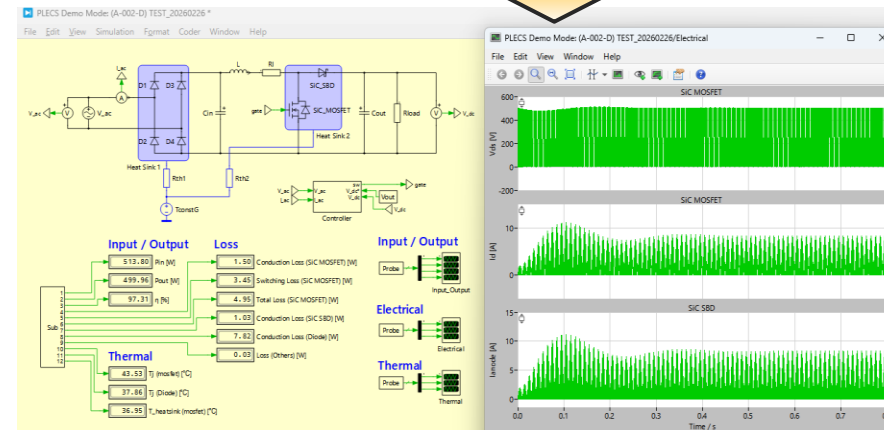
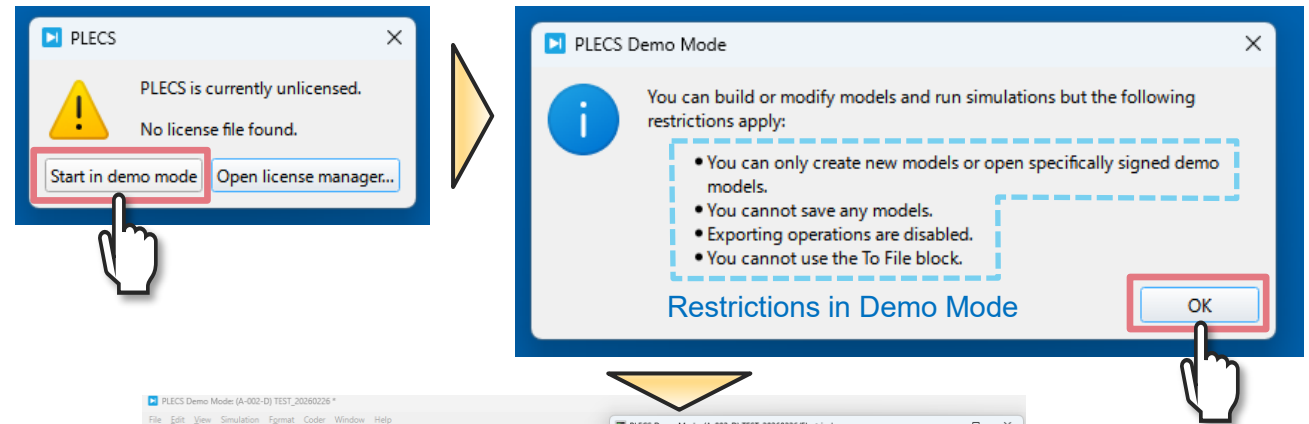
1. Obtaining the Software

If you do not have PLECS installed, please download the installer from the official website and complete the setup process.

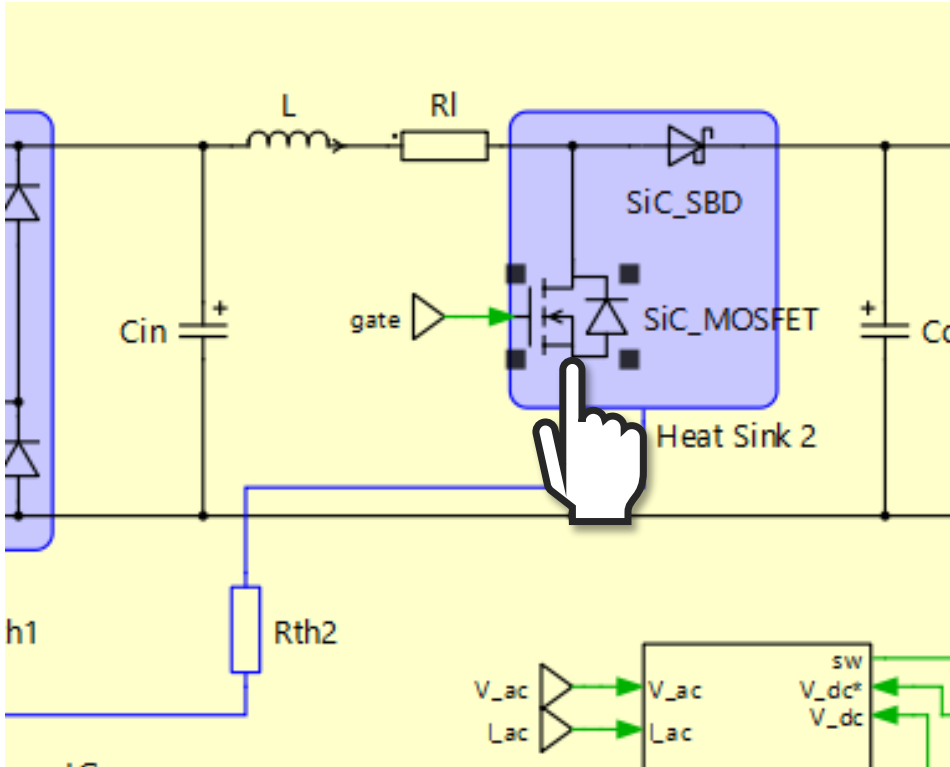
<https://www.plexim.com/download>

2. Licensing (Using Demo Mode)

This reference circuit can be executed and viewed in "Demo Mode" even if you do not possess a paid license.



Schematic window



Block Parameters: (A-002-D) AC-DC Boost PFC Diode Rectific... X

SiC-MOSFET (mask)

Model Generated by ROHM
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Date: 21-Jan.-2026

Parameters Assertions

SiC-MOSFET:
SiCMOS

Custom variables:
struct('Rg_on', 'Rg_on', 'Rg_off', 'Rg_off', 'sw', 'sw')

Gate resistance (on):
Rg_on

Gate resistance (off):
Rg_off

Initial temperature:
T_init

Initial Ron:
Ron_init

OK Cancel Apply Help

- From library...
- By reference
- Edit...
- Remove
- New thermal description...
- New thermal package description...

[SiC-MOSFET] TO-247-4L_750V_25A_65mΩ (SCT4065DR)
[SiC-MOSFET] TO-247-4L_750V_34A_45mΩ (SCT4045DR)
[SiC-MOSFET] TO-247-4L_750V_42A_36mΩ (SCT4036DR)
[SiC-MOSFET] TO-247-4L_750V_56A_26mΩ (SCT4026DR)
[SiC-MOSFET] TO-247N_1200V_19A_90mΩ (SCT4090KE)
[SiC-MOSFET] TO-247N_1200V_26A_62mΩ (SCT4062KE)
[SiC-MOSFET] TO-247N_1200V_32A_50mΩ (SCT4050KE)
[SiC-MOSFET] TO-247N_1200V_40A_36mΩ (SCT4036KE)
[SiC-MOSFET] TO-247N_1200V_81A_18mΩ (SCT4018KE)
[SiC-MOSFET] TO-247N_750V_105A_13mΩ (SCT4013DE)
[SiC-MOSFET] TO-247N_750V_25A_65mΩ (SCT4065DE)
[SiC-MOSFET] TO-247N_750V_34A_45mΩ (SCT4045DE)
[SiC-MOSFET] TO-247N_750V_42A_36mΩ (SCT4036DE)
[SiC-MOSFET] TO-247N_750V_56A_26mΩ (SCT4026DE)
[SiC-MOSFET] TO-263-7LA_1200V_17A_90mΩ (SCT4090KWA)
[SiC-MOSFET] TO-263-7LA_1200V_24A_62mΩ (SCT4062KWA)
[SiC-MOSFET] TO-263-7LA_1200V_29A_50mΩ (SCT4050KWA)
[SiC-MOSFET] TO-263-7LA_1200V_40A_36mΩ (SCT4036KWA)
[SiC-MOSFET] TO-263-7LA_1200V_75A_18mΩ (SCT4018KWA)
[SiC-MOSFET] TO-263-7LA_750V_22A_65mΩ (SCT4065DWA)
[SiC-MOSFET] TO-263-7LA_750V_31A_45mΩ (SCT4045DWA)
[SiC-MOSFET] TO-263-7LA_750V_38A_36mΩ (SCT4036DWA)
[SiC-MOSFET] TO-263-7LA_750V_51A_26mΩ (SCT4026DWW)
[SiC-MOSFET] TOLL_750V_120A_13mΩ (SCT4013DLL)
[SiC-MOSFET] TOLL_750V_26A_65mΩ (SCT4065DLL)
[SiC-MOSFET] TOLL_750V_37A_45mΩ (SCT4045DLL)

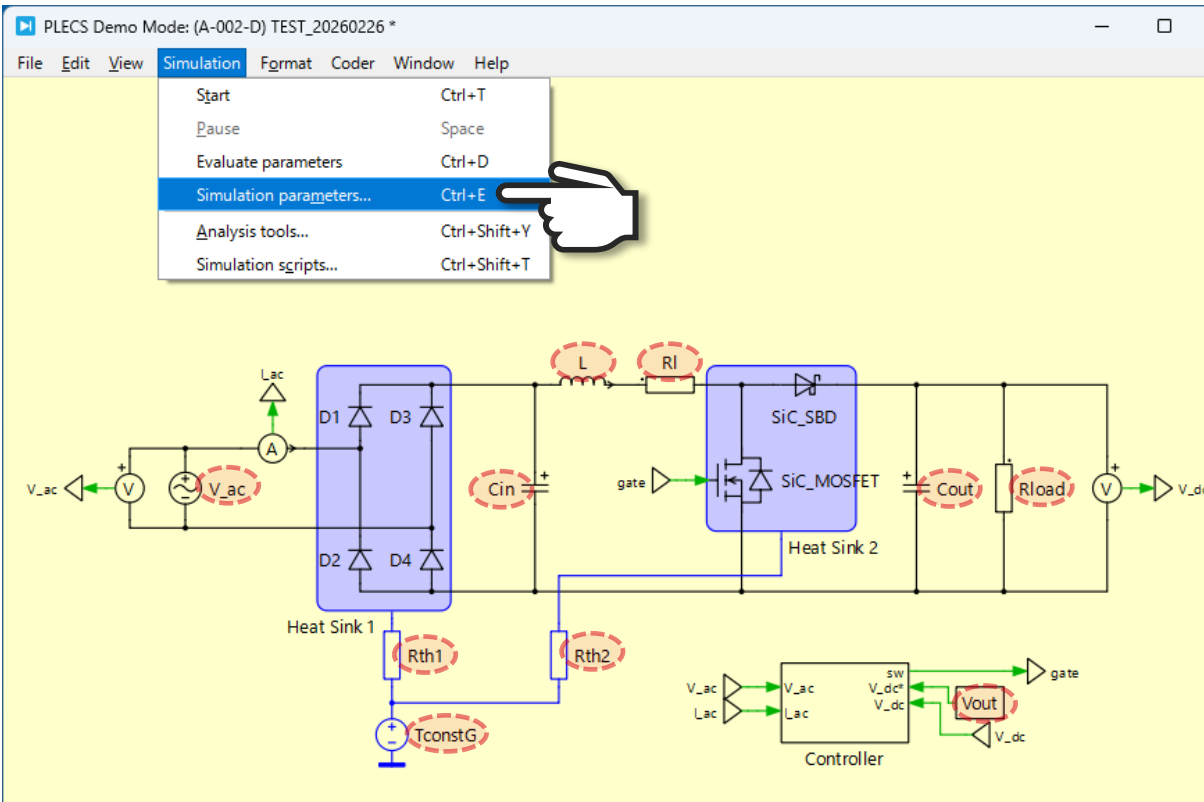
Hover your mouse cursor over the device symbol that you want to change and double-click the left button of the mouse.

Click "... " > "From library..." to view the list of available devices and you can select a favorite device from these.

If the model you need is not in the list, please refer to the application note "[How to Use PLECS Models](#)".

How to change the simulation parameters

Schematic window



```
1 % General|
2 Test time = 0.8; % End time of simulation [s]
3 SiCMOS = 'file:SC14065DR';
4 SiCSBD = 'file:SCS320AG';
5
6 % Grid
7 Vin = 100;
8 %Wac = Vin*sqrt(2); % Grid voltage [V]
9 Vout = 500
10 F = 50.0; % Grid frequency [Hz]
11
12 % Plant
13 fs_k = 50; % Switching frequency [kHz]
14 %fs = fs_k*1e3; % Switching frequency [Hz]
15
16 Rl = 0.001
17 Rload = 500; % Load resistance [ohms]
18 Rsense = 0.0025; % Sense resistance [ohms]
19 L = 1e-3; % Choke inductance [H]
20 Cin = 0.1e-6; % Input capacitor [C]
21 Cout = 1e-3; % Output capacitor [C]
22 C1 = 470e-9; % Reference capacitor [C]
23
24 %Wcout_init = Vout; %Initial Voltage of Output Capacitor [V]
25
26
27 R_Di = 0.02; % Diode On-resistance [ohm]
28 Vf_Di = 0.6; % Diode On-resistance [ohm]
29
30 % Thermal system
31 T_init = 25; % Initial Temperature of Heatsink [deg.C]
32 Thcap_1 = 0.001; % Thermal capacitance of Heatsink [J/K]
33 Thcap_2 = 0.001; % Thermal capacitance of Heatsink [J/K]
34 Rth_1 = 2.0; % Thermal Resistance [K/W]
35 Rth_2 = 2.0; % Thermal Resistance [K/W]
36 Tgnd = 25; %Thermal GND Temperature [deg.C]
37
```

All simulation parameters are parameterized. To modify them, go to the menu, select “Simulation parameters...”, and edit the values within “Model initialization commands.”